

AMENDMENTS TO THE SPECIFICATION

Replace the paragraph beginning on page 12, line 4, with the following:

Figures 1a - ~~1g~~1f show cross sections of a semiconductor memory element arrangement in accordance with an exemplary embodiment of the invention at different states during its fabrication;

Replace the paragraph beginning on page 12, line 7, with the following:

Figures 2a - ~~2g~~2f show cross sections of the semiconductor memory element arrangement from Figure 1 at corresponding states during its fabrication in a perpendicular sectional direction with respect to Figure 1;

Replace the paragraph beginning on page 12, line 7, with the following:

A method for fabricating a semiconductor memory element arrangement in accordance with a preferred exemplary embodiment is explained with reference to Figures ~~1a-g~~1a-f and Figures ~~2a-g~~2a-f, the cross-sectional views illustrated in Figures ~~1a-g~~1a-f and Figures ~~2a-g~~2a-f respectively being illustrated for mutually perpendicular sectional planes.